

KSD288

Power Regulator Low Frequency High Power Amplifier

- Collector-Base Voltage : V_{CBO}=80V
 Collector Dissipation : P_C=25W(T_C=25°C)



1.Base 2.Collector 3.Emitter

NPN Epitaxial Silicon Transistor

Absolute Maximum Ratings T_C=25°C unless otherwise noted

Symbol	Parameter	Value	Units
V _{CBO}	Collector-Base Voltage	80	V
V_{CEO}	Collector-Emitter Voltage	55	V
V _{EBO}	Emitter-Base Voltage	5	V
I _C	Collector Current	3	Α
P _C	Collector Dissipation (T _C =25°C)	25	W
T _J	Junction Temperature	150	°C
T _{STG}	Storage Temperature	- 55 ~ 150	°C

$\textbf{Electrical Characteristics} \ \, \textbf{T}_{\text{C}} = 25^{\circ} \text{C unless otherwise noted}$

Symbol	Parameter	Test Condition	Min.	Тур.	Max.	Units
BV _{CBO}	Collector-Base Breakdown Voltage	I _C =500μA, I _E =0	80			V
BV _{CEO}	Collector-Emitter Breakdown Voltage	I _C =10mA,I _B =0	55			V
BV _{EBO}	Emitter-Base Breakdown Voltage	I _E =500μA, I _C =0	5			V
I _{CBO}	Collector Cut-off Current	$V_{CB}=50V,I_{E}=0$			50	μΑ
h _{FE}	DC Current Gain	$V_{CE}=5V,I_{C}=0.5A$	40		240	
V _{CE} (sat)	Collector-Emitter Saturation Voltage	I _C =1A, I _B =0.1A			1	V

h_{FE} Classification

Classification	R	0	Υ
h _{FE}	40 ~ 80	70 ~ 140	120 ~ 240

Typical Characteristics

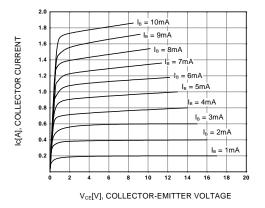


Figure 1. Static Characteristic

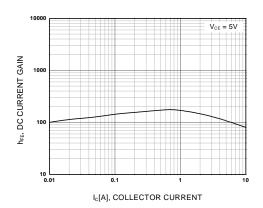


Figure 2. DC current Gain

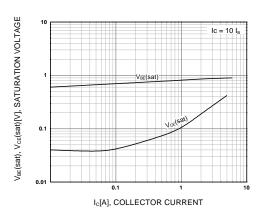


Figure 3. Base-Emitter Saturation Voltage Collector-Emitter Saturation Voltage

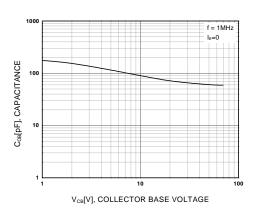


Figure 4. Collector Output Capacitance

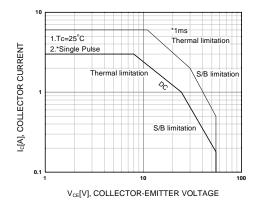


Figure 5. Safe Operating Area

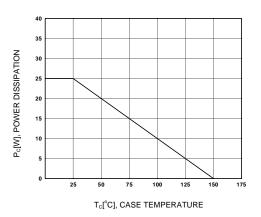
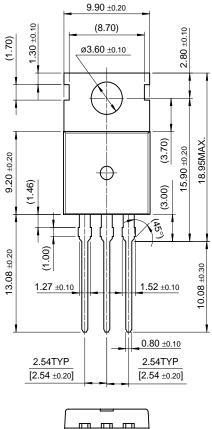


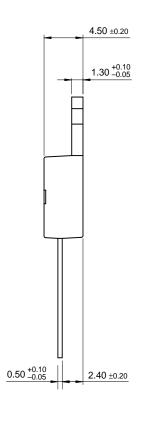
Figure 6. Power Derating

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Package Demensions

TO-220





10.00 ±0.20

Dimensions in Millimeters

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